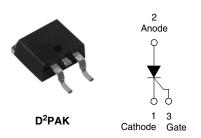


Vishay High Power Products

Surface Mountable Phase Control SCR, 16 A



PRODUCT SUMMARY				
V_{T} at 10 A	< 1.4 V			
I _{TSM}	200 A			
V _{RRM}	1600 V			

DESCRIPTION/FEATURES

The 16TTS16SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology



RoHS*

used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level and lead (Pb)-free ("PbF" suffix).

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	2.5	3.5					
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A				
Aluminum IMS with heatsink, $R_{thCA} = 5 ^{\circ}C/W$	14.0	18.5					

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	10	٨			
I _{RMS}		16	A			
V _{RRM} /V _{DRM}		1600	V			
I _{TSM}		200	А			
V _T	10 A, T _J = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
TJ		- 40 to 125	°C			

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA				
16TTS16SPbF	1600	1600	10				

* Pb containing terminations are not RoHS compliant, exemptions may apply

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
PARAMETER	STMBOL TEST CONDITIONS		TYP.	MAX.		
Maximum average on-state current	I _{T(AV)}	$T_C = 93 \ ^{\circ}C$, 180° conduction, half sine wave	10			
Maximum RMS on-state current	I _{RMS}		1	6	А	
Maximum peak, one-cycle,	1	10 ms sine pulse, rated V_{RRM} applied	17	'0	A	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	200			
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRM} applied	144		A ² s	
	1-1	10 ms sine pulse, no voltage reapplied	200			
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no voltage reapplied		00	A²√s	
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		4	V	
On-state slope resistance	r _t	T 105 %C		.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C	1.1		V	
Maximum reverse and direct lookage aurrent	1 /1	$T_J = 25 \text{ °C}$	0.5			
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_J = 125 \text{ °C}$ $V_R = \text{Rated } V_{RRM} / V_{DRM}$	10	0		
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial $I_T = 1 A$		150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load 200				
Maximum rate of rise of off-state voltage	dV/dt	500		00	V/µs	
Maximum rate of rise of turned-on current	dl/dt	150		60	A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	w	
Maximum average gate power	P _{G(AV)}		2.0	~~~	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	90	mA	
		Anode supply = 6 V, resistive load, T_J = 25 °C	60		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	35		
		Anode supply = 6 V, resistive load, T_J = - 10 °C	3.0	v	
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	2.0		
voltage to trigger		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	v	
Maximum DC gate voltage not to trigger	V_{GD}		0.25		
Maximum DC gate current not to trigger	I _{GD}	$T_{\rm J} = 125 ^{\circ}\text{C}, V_{\rm DRM} = \text{Rated value}$		mA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	$T_J = 25 \ ^{\circ}C$	0.9			
Typical reverse recovery time	t _{rr}	T ₁ = 125 °C	4	μs		
Typical turn-off time	tq	1j=125 C	110			



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THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C	
Soldering temperature	T _S	For 10 s (1.6 mm from case)	240		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.3	°C/W	
Typical thermal resistance, junction to ambient	R _{thJA}	R _{thJA} PCB mount ⁽¹⁾		0/11	
Approvimate weight			2	g	
Approximate weight			0.07	oz.	
Marking device		Case style D ² PAK (SMD-220)	16TTS	16S	

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

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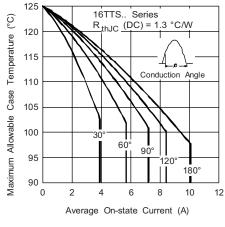


Fig. 1 - Current Rating Characteristics

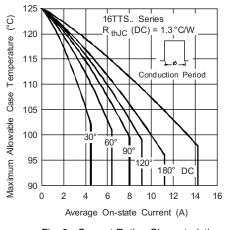


Fig. 2 - Current Rating Characteristics

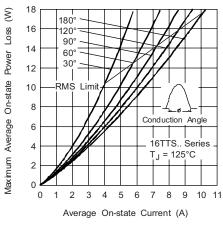


Fig. 3 - On-State Power Loss Characteristics

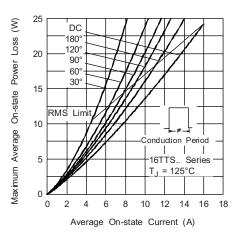


Fig. 4 - On-State Power Loss Characteristics

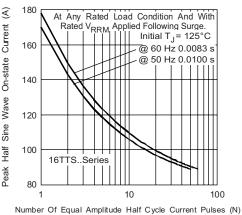


Fig. 5 - Maximum Non-Repetitive Surge Current

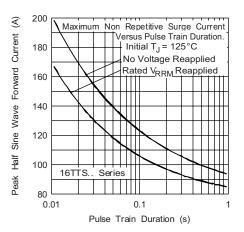


Fig. 6 - Maximum Non-Repetitive Surge Current



Surface Mountable Phase Vishay High Power Products Control SCR, 16 A

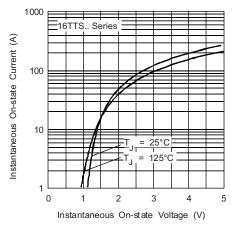
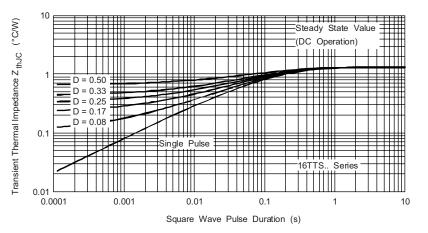


Fig. 7 - On-State Voltage Drop Characteristics





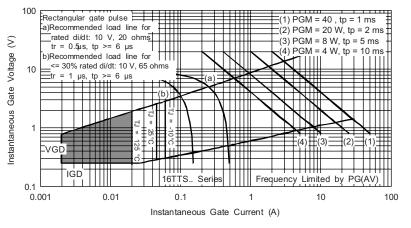


Fig. 9 - Gate Characteristics

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ORDERING INFORMATION TABLE

Device code	16	т	Т	S	16	S	TRL	PbF
		2	3	4	5	6	7	8
	1 -	Cur	rent rati	ng				
	2 -	Circ	uit confi	iguratior	n:			
	_	T =	Single t	hyristor				
	3 -		kage:					
			TO-220					
	4 -		e of silic					
	E			rd recov	-		- \/	(10 -)
	5 -		-	ng: Volta	-			N (16 =)
	6 -		S = TO-220 D ² PAK (SMD-220) version					
	7 -		one = Tu					
		• TF	RL = Tap	e and re	eel (left	orienteo	d)	
		• TF	RR = Tap	be and r	eel (righ	nt orient	ed)	
	8 -	• No	one = St	andard	product	ion		
		• Pb	F = Lea	ad (Pb)-f	ree			

LINKS TO RELATED DOCUMENTS					
Dimensions http://www.vishay.com/doc?95046					
Part marking information	http://www.vishay.com/doc?95054				
Packaging information	http://www.vishay.com/doc?95032				



Vishay

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